# 5 Watt Surmetic<sup>™</sup> 40 Zener Voltage Regulators

This is a complete series of 5 Watt Zener diodes with tight limits and better operating characteristics that reflect the superior capabilities of silicon—oxide passivated junctions. All this in an axial—lead, transfer—molded plastic package that offers protection in all common environmental conditions.

#### **Specification Features:**

- Zener Voltage Range 3.3 V to 200 V
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- Surge Rating of up to 180 W @ 8.3 ms
- Maximum Limits Guaranteed on up to Six Electrical Parameters

#### **Mechanical Characteristics:**

CASE: Void free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are

readily solderable

#### **MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES:**

230°C, 1/16" from the case for 10 seconds **POLARITY:** Cathode indicated by polarity band

**MOUNTING POSITION:** Any

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Max. Steady State Power Dissipation @ T <sub>L</sub> = 75°C, Lead Length = 3/8"	P <sub>D</sub>	5	W
Derate above 75°C		40	mW/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–65 to +200	°C



#### ON Semiconductor®

#### http://onsemi.com





#### **MARKING DIAGRAM**



L = Assembly Location 1N53xxB = Device Code

(See Table Next Page)
Y = Year
WW = Work Week

#### **ORDERING INFORMATION**

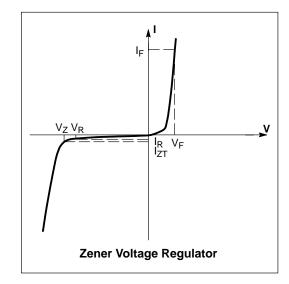
Device	Package	Shipping
1N53xxB	Axial Lead	1000 Units/Box
1N53xxBRL	Axial Lead	4000/Tape & Reel
1N53xxBTA*	Axial Lead	2000/Ammo Pack

<sup>\*1</sup>N5361B Not Available in 2000/Ammo Pack

Devices listed in *bold, italic* are ON Semiconductor **Preferred** devices. **Preferred** devices are recommended choices for future use and best overall value.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted, $V_F = 1.2$ V Max @ $I_F = 1.0$ A for all types)

Symbol	Parameter					
VZ	Reverse Zener Voltage @ I <sub>ZT</sub>					
I <sub>ZT</sub>	Reverse Current					
Z <sub>ZT</sub>	Maximum Zener Impedance @ I <sub>ZT</sub>					
I <sub>ZK</sub>	Reverse Current					
Z <sub>ZK</sub>	Maximum Zener Impedance @ I <sub>ZK</sub>					
I <sub>R</sub>	Reverse Leakage Current @ V <sub>R</sub>					
$V_R$	Breakdown Voltage					
I <sub>F</sub>	Forward Current					
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>					
I <sub>R</sub>	Maximum Surge Current @ T <sub>A</sub> = 25°C					
$\Delta V_{Z}$	Reverse Zener Voltage Change					
I <sub>ZM</sub>	Maximum DC Zener Current					



#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted, V<sub>F</sub> = 1.2 V Max @ I<sub>F</sub> = 1.0 A for all types)

		Zen	er Volta	age (Not	e 7)	Zener Impedance (Note 7)  Leakage Current			I <sub>R</sub>	ΔV <sub>7</sub>	I <sub>ZM</sub>		
Device	Device	V	Z (Volts	s)	@ l <sub>ZT</sub>	Z <sub>ZT</sub> @ I <sub>ZT</sub>	Z <sub>ZK</sub> @ I <sub>ZK</sub>	I <sub>ZK</sub>	I <sub>R</sub> @ V <sub>R</sub>		(Note 8)	(Note 9)	(Note 10)
(Note 6)	Marking	Min	Nom	Max	mA	Ω	Ω	μΑ	μ <b>Α Max</b>	Volts	Α	Volts	mA
1N5363B	1N5363B	28.5	30	31.5	40	8	140	1	0.5	22.8	3.7	0.6	158
1N5364B	1N5364B	31.35	33	34.65	40	10	150	1	0.5	25.1	3.5	0.6	144
1N5365B	1N5365B	34.2	36	37.8	30	11	160	1	0.5	27.4	3.5	0.65	132
1N5366B	1N5366B	37.05	39	40.95	30	14	170	1	0.5	29.7	3.1	0.65	122
1N5367B	1N5367B	40.85	43	45.15	30	20	190	1	0.5	32.7	2.8	0.7	110
1N5368B	1N5368B	44.65	47	49.35	25	25	210	1	0.5	35.8	2.7	0.8	100
1N5369B	1N5369B	48.45	51	53.55	25	27	230	1	0.5	38.8	2.5	0.9	93
1N5370B	1N5370B	53.2	56	58.8	20	35	280	1	0.5	42.6	2.3	1.0	86
1N5371B	1N5371B	57	60	63	20	40	350	1	0.5	45.5	2.2	1.2	79
1N5372B	1N5372B	58.9	62	65.1	20	42	400	1	0.5	47.1	2.1	1.35	76
1N5373B	1N5373B	64.6	68	71.4	20	44	500	1	0.5	51.7	2.0	1.52	70
1N5374B	1N5374B	71.25	75	78.75	20	45	620	1	0.5	56	1.9	1.6	63
1N5375B	1N5375B	77.9	82	86.1	15	65	720	1	0.5	62.2	1.8	1.8	58
1N5376B	1N5376B	82.65	87	91.35	15	75	760	1	0.5	66	1.7	2.0	54.5
1N5377B	1N5377B	86.45	91	95.55	15	75	760	1	0.5	69.2	1.6	2.2	52.5
1N5378B	1N5378B	95	100	105	12	90	800	1	0.5	76	1.5	2.5	47.5
1N5379B	1N5379B	104.5	110	115.5	12	125	1000	1	0.5	83.6	1.4	2.5	43
1N5380B	1N5380B	114	120	126	10	170	1150	1	0.5	91.2	1.3	2.5	39.5
1N5381B	1N5381B	123.5	130	136.5	10	190	1250	1	0.5	98.8	1.2	2.5	36.6
1N5382B	1N5382B	133	140	147	8	230	1500	1	0.5	106	1.2	2.5	34
1N5383B	1N5383B	142.5	150	157.5	8	330	1500	1	0.5	114	1.1	3.0	31.6
1N5384B	1N5384B	152	160	168	8	350	1650	1	0.5	122	1.1	3.0	29.4
1N5385B	1N5385B	161.5	170	178.5	8	380	1750	1	0.5	129	1.0	3.0	28
1N5386B	1N5386B	171	180	189	5	430	1750	1	0.5	137	1.0	4.0	26.4
1N5387B	1N5387B	180.5	190	199.5	5	450	1850	1	0.5	144	0.9	5.0	25
1N5388B	1N5388B	190	200	210	5	480	1850	1	0.5	152	0.9	5.0	23.6

#### 6. TOLERANCE AND TYPE NUMBER DESIGNATION

The JEDEC type numbers shown indicate a tolerance of ±5%.

#### 7. ZENER VOLTAGE ( $V_z$ ) and IMPEDANCE ( $I_{ZT}$ and $I_{ZK}$ )

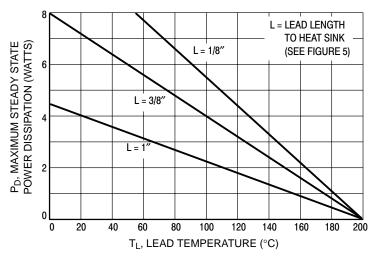
Test conditions for zener voltage and impedance are as follows: Iz is applied 40 ±10 ms prior to reading. Mounting contacts are located 3/8" to 1/2'' from the inside edge of mounting clips to the body of the diode ( $T_A = 25^{\circ}C + 8^{\circ}C, -2^{\circ}C$ ).

#### 8. SURGE CURRENT (I<sub>R</sub>)

Surge current is specified as the maximum allowable peak, non-recurrent square-wave current with a pulse width, PW, of 8.3 ms. The data given in Figure 6 may be used to find the maximum surge current for a square wave of any pulse width between 1 ms and 1000 ms by plotting the applicable points on logarithmic paper. Examples of this, using the 3.3 V and 200 V zener are shown in Figure 7. Mounting contact located as specified in Note 7 ( $T_A = 25^{\circ}\text{C} + 8^{\circ}\text{C}, -2^{\circ}\text{C}$ ). 9. **VOLTAGE REGULATION** ( $\Delta V_Z$ )

The conditions for voltage regulation are as follows: V<sub>Z</sub> measurements are made at 10% and then at 50% of the I<sub>Z</sub> max value listed in the electrical characteristics table. The test current time duration for each V<sub>Z</sub> measurement is 40 ±10 ms. Mounting contact located as specified in Note 7 ( $T_A = 25^{\circ}\text{C} + 8^{\circ}\text{C}, -2^{\circ}\text{C}$ ). 10. MAXIMUM REGULATOR CURRENT ( $I_{ZM}$ )

The maximum current shown is based on the maximum voltage of a 5% type unit, therefore, it applies only to the B-suffix device. The actual I<sub>ZM</sub> for any device may not exceed the value of 5 watts divided by the actual V<sub>Z</sub> of the device. T<sub>L</sub> = 75°C at 3/8" maximum from the device



**Figure 1. Power Temperature Derating Curve** 

#### **TEMPERATURE COEFFICIENTS**

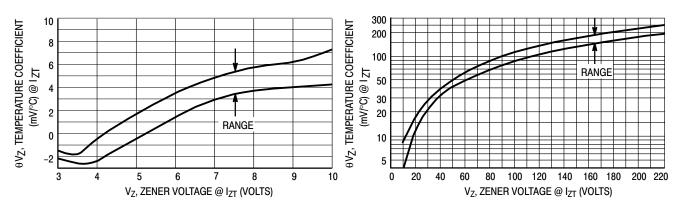


Figure 2. Temperature Coefficient-Range for Units 3 to 10 Volts

Figure 3. Temperature Coefficient-Range for Units 10 to 220 Volts

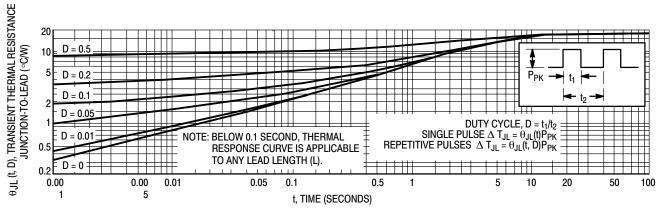


Figure 4. Typical Thermal Response L, Lead Length = 3/8 Inch

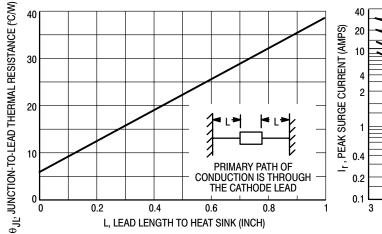


Figure 5. Typical Thermal Resistance

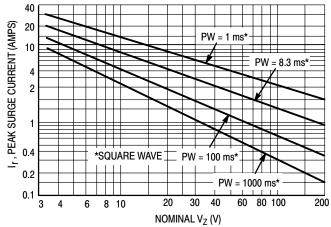


Figure 6. Maximum Non-Repetitive Surge Current versus Nominal Zener Voltage (See Note 3)

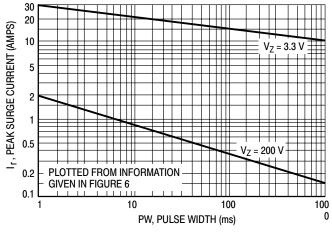


Figure 7. Peak Surge Current versus Pulse Width (See Note 3)

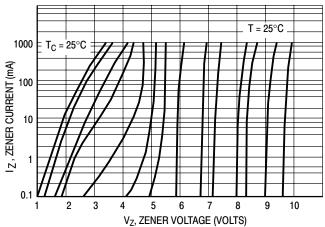


Figure 8. Zener Voltage versus Zener Current  $V_Z = 3.3 \text{ thru } 10 \text{ Volts}$ 

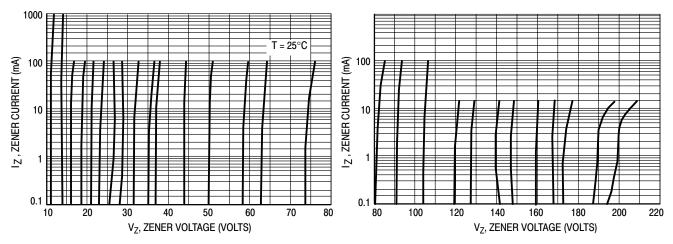


Figure 9. Zener Voltage versus Zener Current  $V_Z = 11$  thru 75 Volts

Figure 10. Zener Voltage versus Zener Current  $V_Z = 82 \text{ thru } 200 \text{ Volts}$ 

#### **APPLICATION NOTE**

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T<sub>L</sub>, should be determined from:

$$\mathsf{T}_\mathsf{L} = \theta_\mathsf{LA} \; \mathsf{P}_\mathsf{D} + \mathsf{T}_\mathsf{A}$$

 $\theta_{LA}$  is the lead-to-ambient thermal resistance and  $P_D$  is the power dissipation.

Junction Temperature, T<sub>J</sub>, may be found from:

$$T_J = T_L + \Delta T_{JL}$$

 $\Delta T_{JL}$  is the increase in junction temperature above the lead temperature and may be found from Figure 4 for a train of power pulses or from Figure 5 for dc power.

$$\Delta T_{JL} = \theta_{JL} P_D$$

For worst-case design, using expected limits of  $I_Z$ , limits of  $P_D$  and the extremes of  $T_J$  ( $\Delta T_J$ ) may be estimated. Changes in voltage,  $V_Z$ , can then be found from:

$$\Delta V = \theta_{VZ} \Delta T_{J}$$

 $\theta_{VZ}$ , the zener voltage temperature coefficient, is found from Figures 2 and 3.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

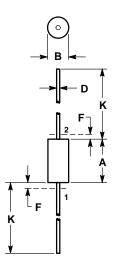
Data of Figure 4 should not be used to compute surge capability. Surge limitations are given in Figure 6. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots resulting in device degradation should the limits of Figure 6 be exceeded.

#### **OUTLINE DIMENSIONS**

### Zener Voltage Regulators – Axial Leaded

### 5 Watt DO-41 Surmetic<sup>™</sup> 40

AXIAL LEAD CASE 17-02 ISSUE C



## NOTES: 1. LEAD DIAMETER AND FINISH NOT CONTROLLED WITHIN DIMENSION F.

	INC	HES	MILLIMETERS				
DIM	MIN	MAX	MIN	MAX			
Α	0.330	0.350	8.38	8.89			
В	0.130	0.145	3.30	3.68			
D	0.037	0.043	0.94	1.09			
F		0.050		1.27			
K	1.000	1.250	25.40	31.75			

STYLE 1: PIN 1. ANODE

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